

- purging the second reactant from the reactor with an inert gas;
pulsing a third reactant pulse into the reactor, the third reactant comprising a volatile titanium compound; and
purging the third reactant from the reactor with an inert gas.
29. (New) The method of Claim 28, wherein no more than one molecular layer is deposited onto the substrate per growth cycle.
30. (New) The method of Claim 28, wherein the first reactant is a cyclopentadienyl compound of strontium.
31. (New) The method of Claim 30, wherein the growth cycle further comprises:
pulsing a fourth reactant pulse into the reactor, the fourth reactant comprising a cyclopentadienyl compound of barium; and
purging the fourth reactant from the reactor with an inert gas.
32. (New) The method of Claim 30, wherein the growth cycle is conducted in a sequence in which the first reactant is pulsed first, the second reactant is pulsed second and the third reactant is pulsed after the second reactant.
33. (New) The method of Claim 30, wherein the growth cycle is conducted in a sequence in which the third reactant is pulsed first, the second reactant is pulsed second, the first reactant is pulsed third, and the second reactant is pulsed fourth.
34. (New) The method of Claim 28, wherein the first reactant is a cyclopentadienyl compound of barium.
35. (New) The method of Claim 34, wherein each cycle further comprises:
pulsing a fourth reactant pulse into the reactor, the fourth reactant comprising a cyclopentadienyl compound of strontium; and
removing the fourth reactant from the reactor with an inert gas.
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REMARKS

New Claims

Applicants have added Claims 28-35 to better protect what Applicant regards as the invention. These new claims are fully supported by the specification, as filed. *See, e.g.,* p. 2, ll. 24-33; p. 4, ll. 25-30; p. 7, ll. 6-11; p. 10, ll. 20-31.